

GigaDevice Semiconductor Inc.

GD32C2x1 系列 FLASH 模拟 EEPROM

应用笔记

AN213

1.1 版本

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1. 简介

FLASH 和 EEPROM 都是非易失性存储器，在掉电后数据还会保留。FLASH 和 EEPROM 最大的区别是擦除方式不同，EEPROM 可以按字节进行擦除，但 FLASH 最小擦除单位是页，一页通常包含多个字节甚至几 K 字节。FLASH 和 EEPROM 擦写属性决定了 EEPROM 容量小但擦写寿命比较高，而 FLASH 容量非常大，但擦写寿命短。

在 MCU 主频高的情况下，可以采用 FLASH 模拟 EEPROM 来降低成本。本文介绍了一种采用 FLASH 模拟 EEPROM 的方法，实现了 EEPROM 按字节进行数据修改，可防止复位或掉电产生的数据丢失，当采用的 FLASH 存储空间越大，EEPROM 性能越好。

2. EEPROM 备份区结构

本文以GD32C2X1的后33页FLASH模拟2K字节EEPROM来介绍FLASH模拟EEPROM的方法。

2.1. GD32C2x1 FLASH 简介

GD32C2x1提供高达64KB片上FLASH。本文使用的GD32C2X1闪存基地址和大小如[表2-1. GD32C2x1 64KB 闪存基地址和大小](#)所示。

表 2-1. GD32C2x1 64KB 闪存基地址和大小

闪存块	名称	地址范围	大小（字节）
主存储闪存块	第0页	0x0800 0000 – 0x0800 03FF	1KB
	第1页	0x0800 0400 – 0x0800 07FF	1KB
	第2页	0x0800 0800 – 0x0800 0BFF	1KB
	.		
	第63页	0x0800 FC00 - 0x0800 FFFF	1KB
信息块	引导装载程序	0x1FFF 0000 - 0x1FFF 0BFF	3KB
选项字节块	选项字节	0x1FFF 7800 - 0x1FFF 787F	128B
一次性编程块	OTP字节	0x1FFF 7000~0x1FFF 73FF	1KB

2.2. EEPROM 数据备份结构

表 2-2. EEPROM 页数据备份存储结构

功能		大小（字节）
EEPROM 页 0	FLASH 页使用标记	8
	EEPROM 页开始标记	8
	EEPROM 页结束标记	8
	EEPROM 数据	2048
EEPROM 页 1	FLASH 页使用标记	8
	EEPROM 页开始标记	8
	EEPROM 页结束标记	8
	EEPROM 数据	2048
...	...	...
EEPROM 页 n	FLASH 页使用标记	8
	EEPROM 页开始标记	8
	EEPROM 页结束标记	8
	EEPROM 数据	2048

3. FLASH 模拟 EEPROM 方案

3.1. 算法实现

3.1.1. 参数宏

表 3-1. 参数宏

名称	功能
EEPROM_DATA_SIZE	模拟 EEPROM 大小
EEPROM_FLASH_PAGE_NUM	使用的 FLASH 页数
FLASH_PAGE_SIZE	FLASH 页大小
EEPROM_PAGE_SIZE	EEPROM 页大小
EEPROM_PAGE_DW_NUM	每页 EEPROM 包含的双字数
EEPROM_BACKUP_SIZE	EEPROM 备份区大小
EEPROM_BACKUP_END_ADDR	EEPROM 备份区结束地址
EEPROM_BACKUP_START_ADDR	EEPROM 备份区起始地址
EEPROM_PAGE_HEAD_FLAG	EEPROM 起始标记
EEPROM_PAGE_END_FLAG	EEPROM 结束标记
EEPROM_WORK_PAGE_FLAG	FLASH 页使用标记
FLASH_PAGES_PER_EEPROM_PAGE	每页 EEPROM 包含的 FLASH 页数

3.1.2. API 函数

函数 eeprom_init

函数 eeprom_init 用于初始化 EEPROM 备份区, 并获取当前正在用于 EEPROM 备份的 FLASH 页相对编号。

表 3-2. EEPROM 初始化

```
void eeprom_init(void)
{
    uint16_t i = 0;
    uint8_t flag_mark_num = 0;
    uint64_t flag_work_page = 0;
    uint8_t check_ff_flag = 0;
    for(i = 0; i < EEPROM_FLASH_PAGE_NUM; i += FLASH_PAGES_PER_EEPROM_PAGE) {
        flag_work_page = REG64(EEPROM_BACKUP_START_ADDR + i * FLASH_PAGE_SIZE);
        check_ff_flag = check_ff(EEPROM_BACKUP_START_ADDR + i * FLASH_PAGE_SIZE,
        FLASH_PAGE_SIZE * FLASH_PAGES_PER_EEPROM_PAGE);
        /* if the flash is without EEPROM_WORK_PAGE_FLAG but the page is not empty, erase
        the flash page */
    }
```



```

        if(((0xffffffffffff == flag_work_page) && (0x01 != check_ff_flag)) || ((0xffffffffffff !=
flag_work_page) && (EEPROM_WORK_PAGE_FLAG != flag_work_page))) {
            eeprom_block_erase(EEPROM_BACKUP_START_ADDR + i * FLASH_PAGE_SIZE);
        } else if(REG64(EEPROM_BACKUP_START_ADDR + i * FLASH_PAGE_SIZE) ==
EEPROM_WORK_PAGE_FLAG) {
            /* find the flash page with EEPROM_WORK_PAGE_FLAG marked */
            current_page = i;
            flag_mark_num++;
        }
    }
    /* no EEPROM_WORK_PAGE_FLAG is found */
    if(flag_mark_num == 0) {
        current_page = 0;
    }
    if(flag_mark_num > 1) {
        /* the first block is not the marked page */
        if(REG64(EEPROM_BACKUP_START_ADDR) == 0xffffffffffff) {
            if(REG64(EEPROM_BACKUP_START_ADDR + current_page * FLASH_PAGE_SIZE
+ 8 * 2) == EEPROM_PAGE_END_FLAG) {
                /* erase the page whose index is current_page-
FLASH_PAGES_PER_EEPROM_PAGE(the forward EEPROM block) */
                eeprom_block_erase(EEPROM_BACKUP_START_ADDR + (current_page -
FLASH_PAGES_PER_EEPROM_PAGE)*FLASH_PAGE_SIZE);
            } else {
                /* erase the page whose index is current_page, because
EEPROM_PAGE_END_FLAG is not found, and the data is incomplete, discard the data */
                eeprom_block_erase(EEPROM_BACKUP_START_ADDR + current_page *
FLASH_PAGE_SIZE);
                current_page -= FLASH_PAGES_PER_EEPROM_PAGE;
            }
        }
        /* the first block is the marked block */
    } else {
        /* the marked block is the first block and the last block */
        if(FLASH_PAGES_PER_EEPROM_PAGE != current_page) {
            if(REG64(EEPROM_BACKUP_START_ADDR + 8 * 2) ==
EEPROM_PAGE_END_FLAG) {
                eeprom_block_erase(EEPROM_BACKUP_START_ADDR + current_page *
FLASH_PAGE_SIZE);
                current_page = 0;
            } else {
                eeprom_block_erase(EEPROM_BACKUP_START_ADDR);
            }
        }
        /* the marked block is the first block and the second block */
    }
}

```

函数 eeprom_write

表 3-3. EEPROM 写函数

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```

    }else{
        current_page = current_page + FLASH_PAGES_PER_EEPROM_PAGE;
    }
}
block_addr = EEPROM_BACKUP_START_ADDR + current_page * FLASH_PAGE_SIZE + 8;
ee_data_addr = block_addr + 8 * 2;
temp_flag = EEPROM_WORK_PAGE_FLAG;
if(0 == flash_program(block_addr - 8, &temp_flag, 1)) {
    ee_state = 0x00;
}
/* write the EEPROM_PAGE_HEAD_FLAG */
temp_flag = EEPROM_PAGE_HEAD_FLAG;
if(0 == flash_program(ee_data_addr - 8 * 2, &temp_flag, 1)) {
    ee_state = 0x00;
}
/* write the data */
if(0 == flash_program(ee_data_addr, record_buf, EEPROM_PAGE_DW_NUM)) {
    ee_state = 0x00;
}
/* read back data */
flash_read_word(ee_data_addr, (uint8_t *)record_buf, EEPROM_DATA_SIZE);
tmp_size = size;
addr_tmp = ee_addr;
while(tmp_size--) {
    /* check the data */
    if(((uint8_t *)record_buf)[addr_tmp++] != *data++) {
        ee_state = 0x00;
    }
}
/* write the EEPROM_PAGE_END_FLAG */
if(ee_state == 0x01) {
    temp_flag = EEPROM_PAGE_END_FLAG;
    if(0 == flash_program(ee_data_addr - 8, &temp_flag, 1)) {
        ee_state = 0x00;
    }
}
if(ee_data_addr == block_addr + 8 * 2) {
    if(block_addr == EEPROM_BACKUP_START_ADDR + 8) {
        /* the current page is the last flash page */
        eeprom_block_erase(EEPROM_BACKUP_START_ADDR +
            (EEPROM_FLASH_PAGE_NUM - FLASH_PAGES_PER_EEPROM_PAGE)*FLASH_PAGE_SIZE);
    } else {
        /* the current page is not the last flash page */

```

```

        eeprom_block_erase(EEPROM_BACKUP_START_ADDR + (current_page -
FLASH_PAGES_PER_EEPROM_PAGE)*FLASH_PAGE_SIZE);
    }
}
return ee_state;
}

```

函数 eeprom_read

函数 eeprom_read 用于读取 EEPROM 备份区最新的数据。注意该函数的入参 ee_addr 是 EEPROM 地址，范围为 0-2047。

表 3-4. EEPROM 读函数

```

uint8_t eeprom_read(uint16_t ee_addr, uint8_t *data, uint16_t size)
{
    uint8_t ee_state = 1, i = 0;
    uint32_t page_addr, ee_data_addr;
    /* find the page start address to write data */
    page_addr = EEPROM_BACKUP_START_ADDR + current_page * FLASH_PAGE_SIZE + 8;
    /* locate at the address to read data */
    ee_data_addr = page_addr + 8 * 2;
    if(ee_addr + size > EEPROM_DATA_SIZE) {
        ee_state = 0x00;
        size = EEPROM_DATA_SIZE - ee_addr;
    }
    /* read data */
    flash_read_word(ee_data_addr + ee_addr, data, size);
    return(ee_state);
}

```

3.1.3. 测试结果

测试在 EEPROM 中改写第一个字节共 16 次。写入数据如 [图 3-1. 读写数据](#) 所示。

图 3-1. 读写数据

```

uint8_t data[2048] = {0x00, 0x01, 0x02, 0x03, 0x04, 0x05, 0x06, 0x07, 0x08, 0x09, 0x0A, 0x0B, 0x0C, 0x0D, 0x0E, 0x0F,
.....0x10, 0x11, 0x12, 0x13, 0x14, 0x15, 0x16, 0x17, 0x18, 0x19, 0x1A, 0x1B, 0x1C, 0x1D, 0x1E, 0x1F
.....};

```

代码如 [表 3-5. 测试 demo](#) 所示。

表 3-5. 测试 demo

```

int main(void)
{
    gd_eval_led_init(LED1);
    gd_eval_led_init(LED2);
    eeprom_init();
}

```

```

    eeprom_read(0, data_read, 2048);
    for(int i=0; i<16; i++){
        data[0] = i;
        eeprom_write(0, data, 2048);
        eeprom_read(0, data_read, 2048);
        if(SUCCESS != byte_memory_compare(data, data_read, 2048)) {
            gd_eval_led_on(LED2);
            return ERROR;
        }
    }
    gd_eval_led_on(LED1);
    while(1) {
    }
}

```

测试结果如图3-2. EEPROM 备份区数据所示。

图 3-2. EEPROM 备份区数据

[illegible]

4. 版本历史

表 4-1. 版本历史

版本号.	说明	日期
1.0	首次发布	2024 年 06 月 03 日
1.1	更新版权声明信息	2025 年 06 月 03 日

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